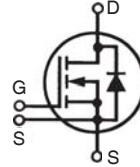


X3-Class HiPerFET™ Power MOSFET

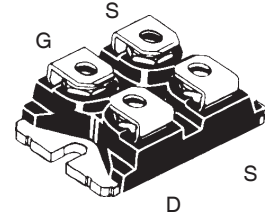
IXFN170N25X3

$$\begin{aligned} V_{DSS} &= 250V \\ I_{D25} &= 146A \\ R_{DS(on)} &\leq 7.4m\Omega \end{aligned}$$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



miniBLOC, SOT-227
 E153432



G = Gate
S = Source
D = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	250	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	250	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	146	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	400	A
I_A	$T_C = 25^\circ\text{C}$	85	A
E_{AS}	$T_C = 25^\circ\text{C}$	2.3	J
P_D	$T_C = 25^\circ\text{C}$	390	W
dv/dt	$I_S \leq I_{DM}, V_{DD} \leq V_{DSS}, T_J \leq 150^\circ\text{C}$	20	V/ns
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ minute}$	2500 V~
	$I_{ISOL} \leq 1\text{mA}$	$t = 1 \text{ second}$	3000 V~
M_d	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
Weight		30	g

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500 V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 1mA$	250		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 4mA$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			10 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 85A$, Note 1	6.1		7.4 m Ω

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	$V_{DS} = 10V, I_D = 60A$, Note 1	66	110	S
R_{Gi}	Gate Input Resistance		1.3	Ω
C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		13.5	nF
C_{oss}			2.3	nF
C_{rss}			1.6	pF
Effective Output Capacitance				
$C_{o(er)}$	Energy related	$V_{GS} = 0V$ $V_{DS} = 0.8 \cdot V_{DSS}$	800	pF
$C_{o(tr)}$	Time related		3280	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 85A$ $R_G = 5\Omega$ (External)		18	ns
t_r			10	ns
$t_{d(off)}$			62	ns
t_f			7	ns
$Q_{g(on)}$	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 85A$		190	nC
Q_{gs}			55	nC
Q_{gd}			45	nC
R_{thJC}				0.32 °C/W
R_{thCS}		0.05		°C/W

Source-Drain Diode

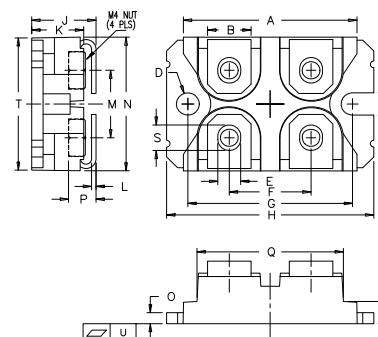
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0V$			170 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			680 A
V_{SD}	$I_F = 100A, V_{GS} = 0V$, Note 1			1.4 V
t_{rr}	$I_F = 85A, -di/dt = 100A/\mu s$ $V_R = 100V, V_{GS} = 0V$		135	ns
Q_{RM}			980	nC
I_{RM}			13	A

Note 1. Pulse test, $t \leq 300\mu s$, duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

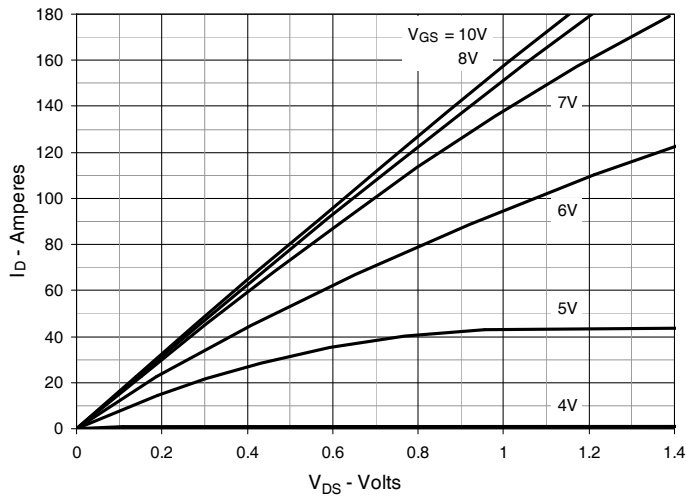
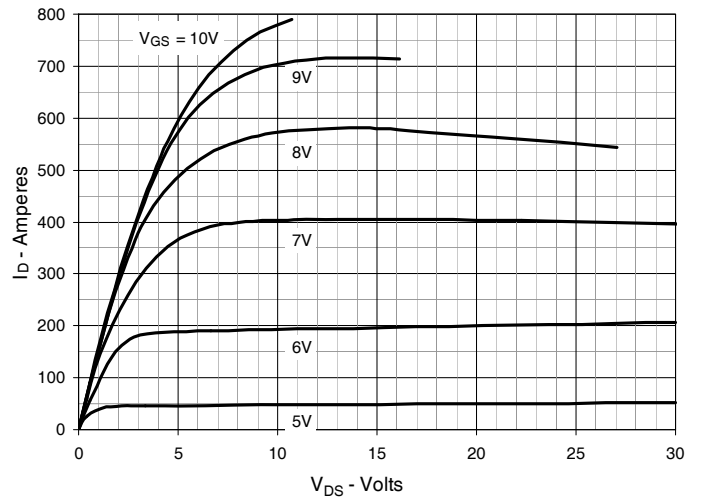
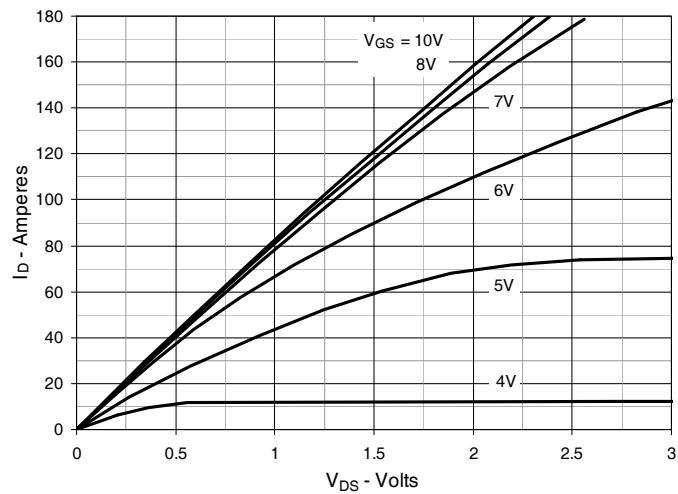
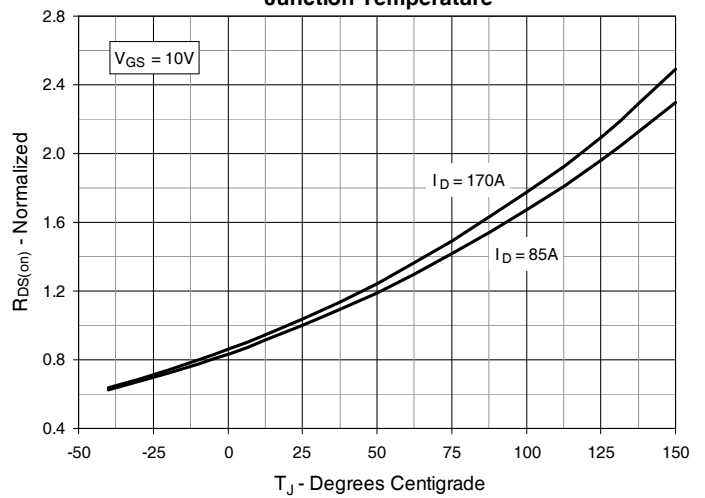
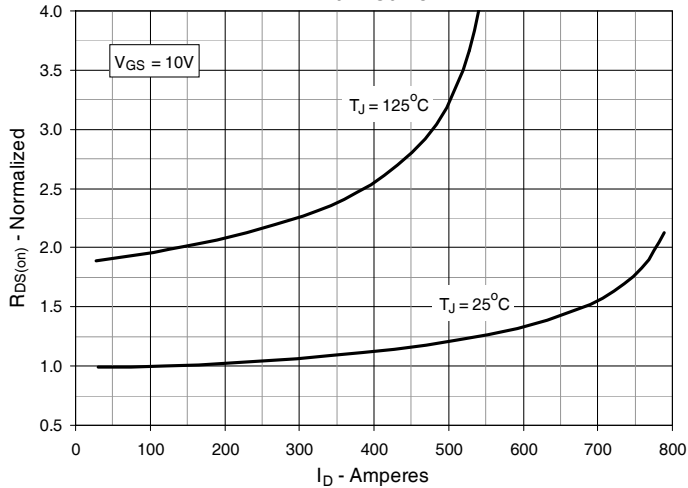
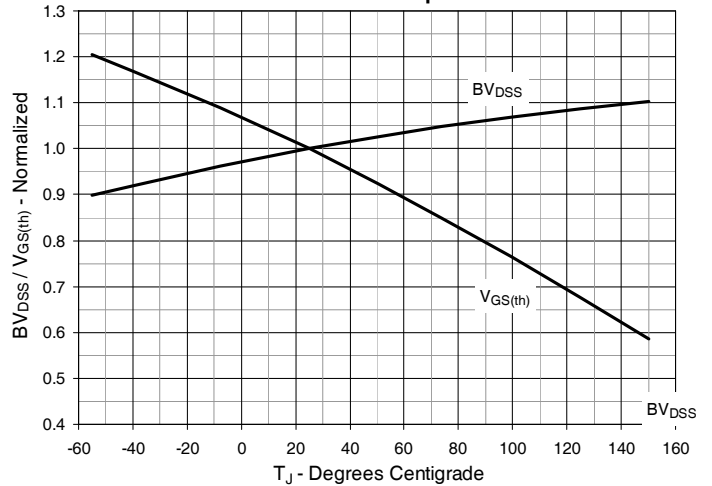
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 85\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 85\text{A}$ Value vs. Drain Current

Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature


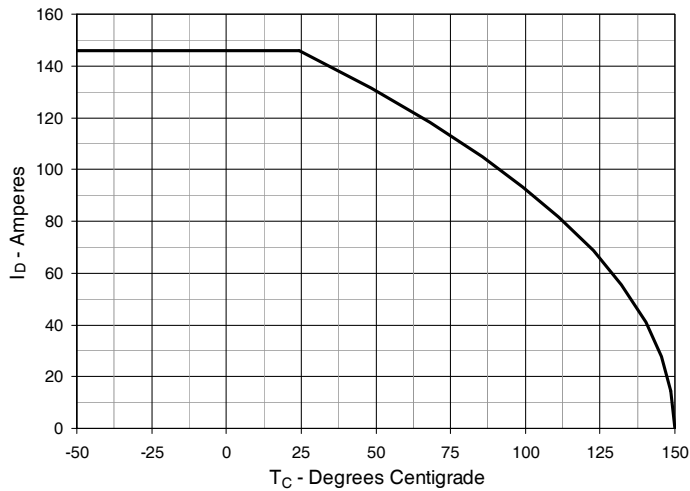
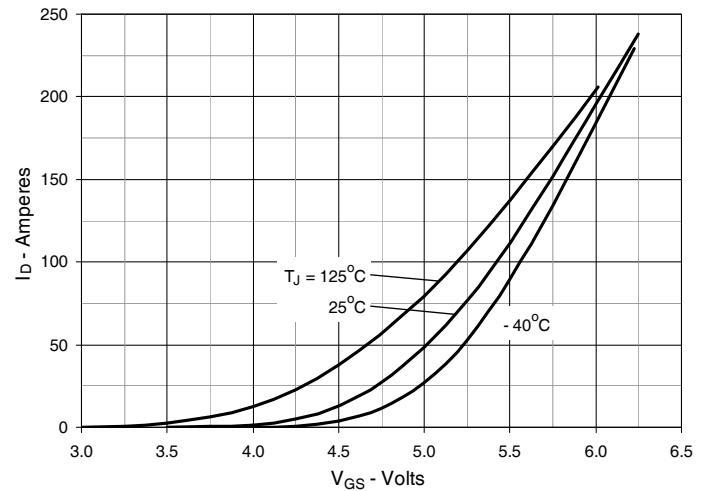
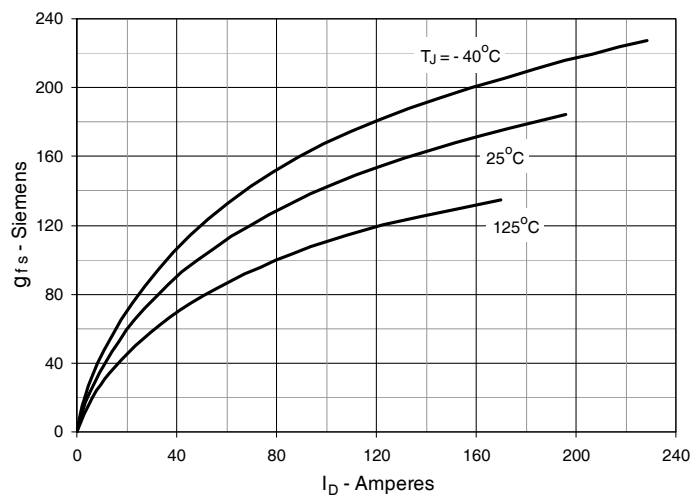
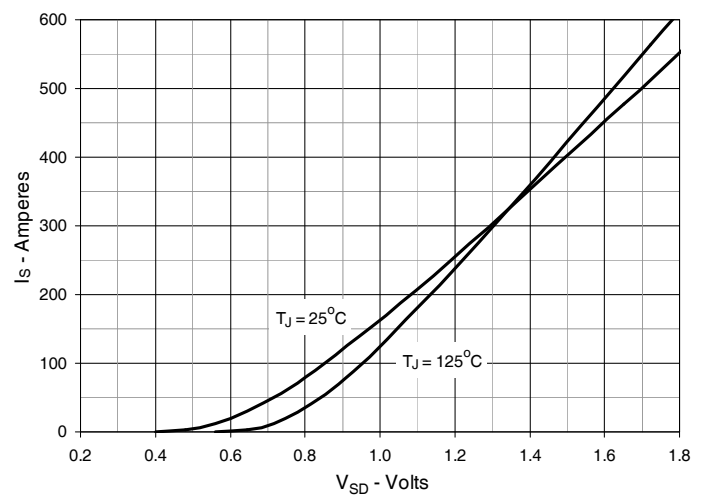
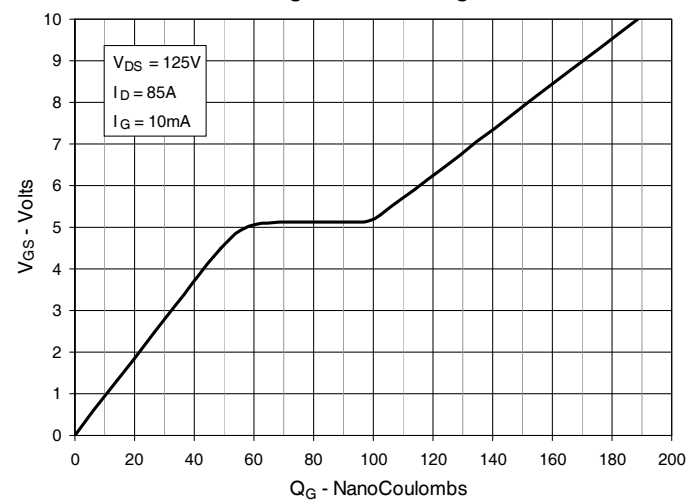
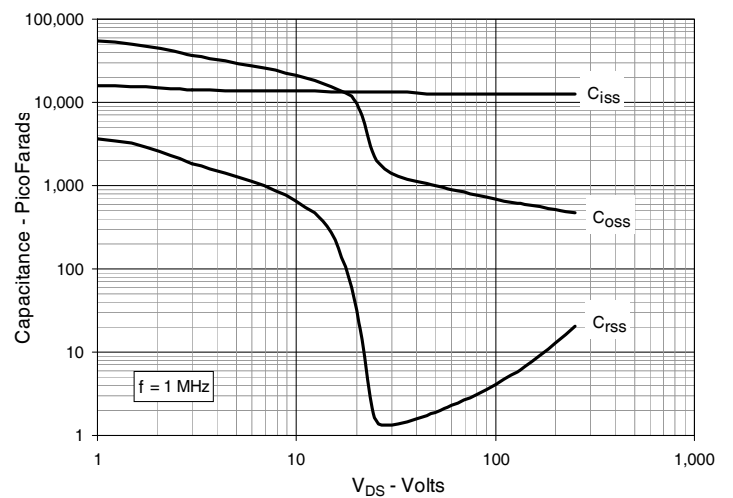
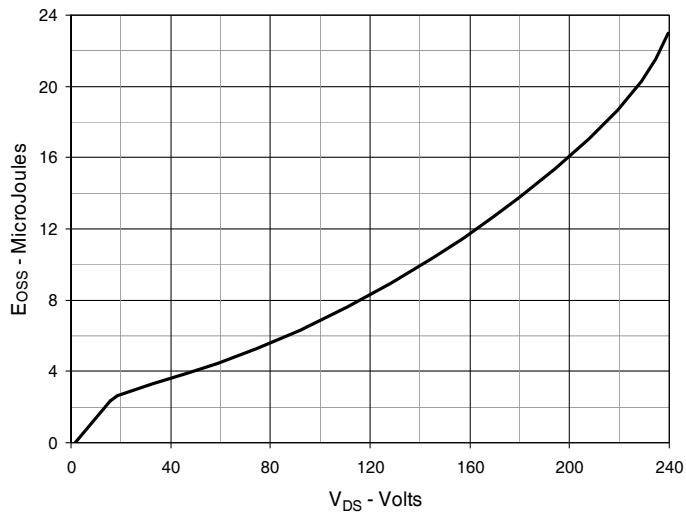
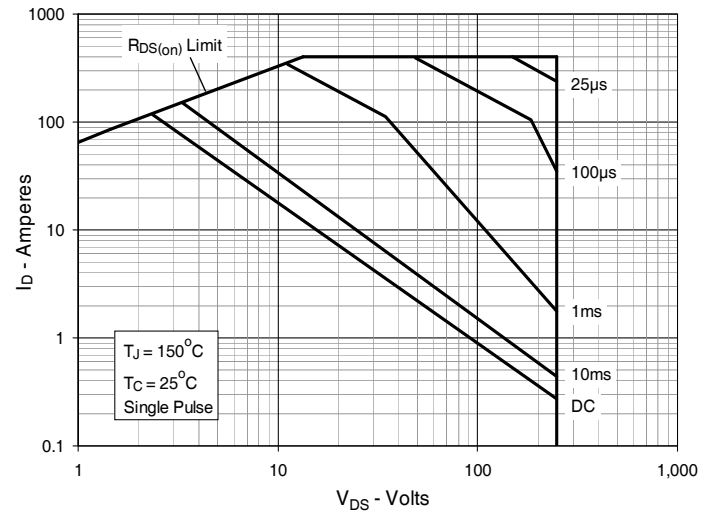
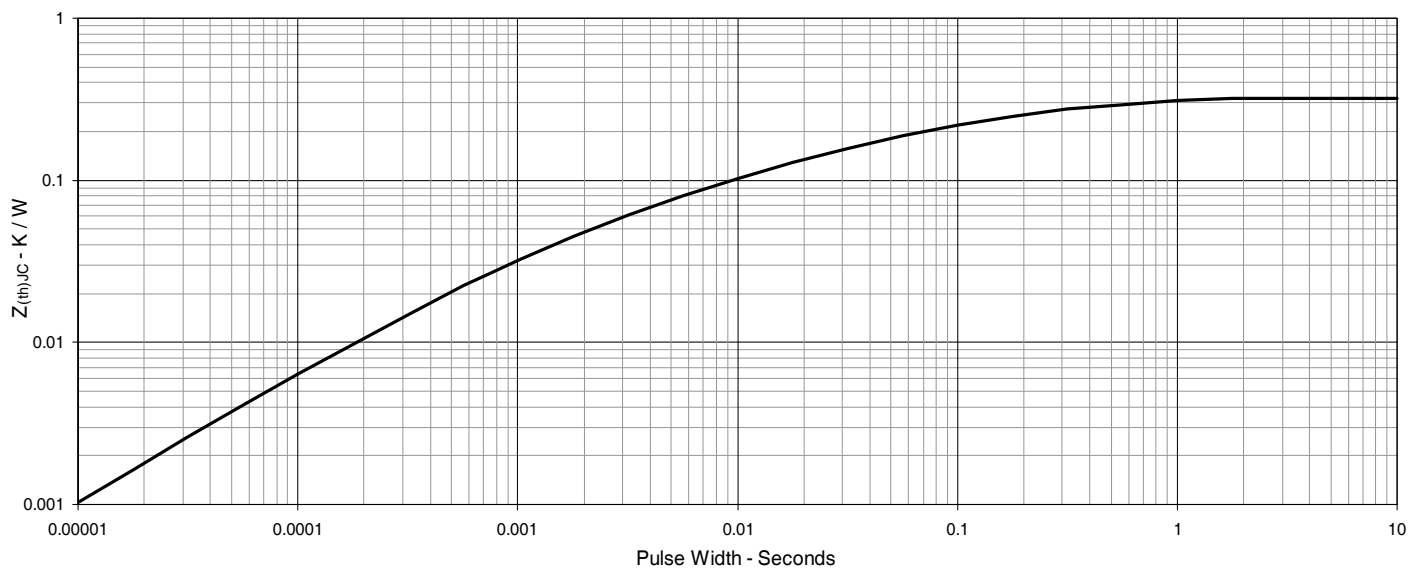
Fig. 7. Maximum Drain Current vs. Case Temperature

Fig. 8. Input Admittance

Fig. 9. Transconductance

Fig. 10. Forward Voltage Drop of Intrinsic Diode

Fig. 11. Gate Charge

Fig. 12. Capacitance


Fig. 13. Output Capacitance Stored Energy

Fig. 14. Forward-Bias Safe Operating Area

Fig. 15. Maximum Transient Thermal Impedance




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